

Appl. No. 09/920,450  
Amdt. dated January 26, 2004  
Reply to Office action of September 26, 2003

In the Claims:

No claims are amended in this response.

1. (previously amended) A defect inspection apparatus for a phase shift mask having a phase shifter pattern provided on a mask transparent substrate, which is characterized in that after said phase shifter pattern has been formed, a phase shifter defect inspection is performed from a mask transparent substrate side of said phase shift mask, which is opposite to a side thereof where said phase shifter pattern has been formed, by applying inspection light to said mask transparent substrate side of said phase shift mask and capturing a reflected light image.

2. (previously amended) A defect inspection apparatus for a phase shift mask according to claim 1, wherein reflection images of at least two different phase shifter pattern fabricated regions are captured, and then respective image signals of the reflection images are compared with each other to detect a defect on the mask from a difference between said signals.

3. (original) A defect inspection apparatus for a phase shift mask according to claim 2, wherein said at least two different phase shifter pattern fabricated regions are phase shifter pattern fabricated regions of chips different from each other.

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4. (original) A defect inspection apparatus for a phase shift mask according to claim 2 or 3, wherein the reflection images of said at least two different phase shifter pattern fabricated regions are captured through respective magnifying optical systems.

5. (original) A defect inspection apparatus for a phase shift mask according to claim 2, wherein said at least two different phase shifter pattern fabricated regions are phase shifter pattern fabricated regions in an identical chip pattern.

6. (original) A defect inspection apparatus for a phase shift mask according to claim 2 or 5, wherein the reflection images of said at least two different phase shifter pattern fabricated regions are captured through an identical magnifying optical system.

7. (previously amended) A defect inspection apparatus for a phase shift mask according to any one of claims 2, 3 or 5, wherein said reflection images obtained by reflected light are dark field images obtained by dark field illumination or bright field images obtained by bright field illumination.

8. (previously presented) A defect inspection apparatus for a phase shift mask according to claim 4, wherein said reflection images obtained by reflected light are dark field

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images obtained by dark field illumination or bright field images obtained by bright field illumination.

9. (previously presented) A defect inspection apparatus for a phase shift mask according to claim 6, wherein said reflection images obtained by reflected light are dark field images obtained by dark field illumination or bright field images obtained by bright field illumination.